

INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		<i>Complete if Known</i>	
		Application Number	Unknown 10/789,041
		Filing Date	Even Date Herewith 2/27/04
		First Named Inventor	Forbes, Leonard
		Group Art Unit	Unknown 2818
		Examiner Name	Unknown PHAN
Sheet 1 of 8		Attorney Docket No: 1303.058US2	

US PATENT DOCUMENTS						
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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		Examiner Name	Unknown PHA/N			
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TP	US-5,740,104	04/14/1998	Forbes, Leonard	365	185.03	01/29/1997
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		Complete If Known <table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 30%; padding: 2px;">Application Number</td> <td colspan="4" style="padding: 2px;">Unknown- 10/789,041</td> </tr> <tr> <td style="padding: 2px;">Filing Date</td> <td colspan="4" style="padding: 2px;">Even Date Herewith 2/27/04</td> </tr> <tr> <td style="padding: 2px;">First Named Inventor</td> <td colspan="4" style="padding: 2px;">Forbes, Leonard</td> </tr> <tr> <td style="padding: 2px;">Group Art Unit</td> <td colspan="4" style="padding: 2px;">Unknown- 2818</td> </tr> <tr> <td style="padding: 2px;">Examiner Name</td> <td colspan="4" style="padding: 2px;">Unknown- PHAN</td> </tr> </table>					Application Number	Unknown- 10/789,041				Filing Date	Even Date Herewith 2/27/04				First Named Inventor	Forbes, Leonard				Group Art Unit	Unknown- 2818				Examiner Name	Unknown- PHAN			
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<i>TP</i>	US-6,232,643	05/15/2001	Forbes, Leonard , et al.	257	405	11/13/1997
	US-6,238,976	05/29/2001	Noble, Wendell P., et al.	438	259	02/27/1998
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TP	US-6,458,701	10/01/2002	Chae, Yun-sook , et al.	438	680	10/12/2000
	US-6,459,618	10/01/2002	Wang, Janet S.	365	185.18	06/13/2001
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	US-6,498,362	12/24/2002	Forbes, Leonard , et al.	257	295	08/26/1999
	US-6,514,828	02/04/2003	Ahn, Kie Y., et al.	438	297	04/20/2001
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	US-6,521,958	02/18/2003	Forbes, L. , et al.	257	391	08/26/1999
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✓	US-6,586,785	07/01/2003	Flagan, Richard C., et al.	257	261	06/29/2001

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		First Named Inventor	Forbes, Leonard
		Group Art Unit	Unknown 2818
		Examiner Name	Unknown PHAN
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